



DCR1260F42

Phase Control Thyristor

DS5966-3 August 2014 (LN31840)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR1260F42 DCR1260F40	4200 4000	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 100\text{mA}, \\ V_{DRM}, V_{RRM}t_p &= 10\text{ms}, \\ V_{DSM}\&V_{RSM} &= \\ V_{DRM}\&V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1260F42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	4200V
$I_{T(AV)}$	1255A
I _{TSM}	16800A
dV/dt*	1500V/µs
dl/dt	1000A/µs

* Higher dV/dt selections available

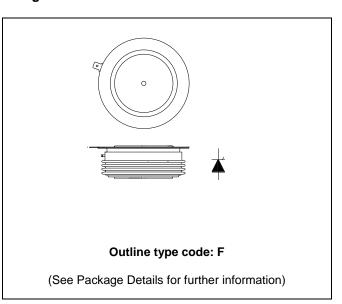


Fig. 1 Package outline





CURRENT RATINGS

$T_{case} = 60$ °C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	1260	Α
I _{T(RMS)}	RMS value	-	1980	А
I _T	Continuous (direct) on-state current	-	1890	Α

SURGE RATINGS

Symbol Parameter		Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	16.8	kA
l ² t	I ² t for fusing	$V_R = 0$	1.41	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.0184	°C/W
		Single side cooled	Anode DC		0.0333	°C/W
			Cathode DC	ı	0.0418	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 23kN	Double side		0.004	°C/W
		(with mounting compound)	Single side	ı	0.008	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}			125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			20.0	25.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ons	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	250	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V _{T(TO)}	Threshold voltage – Low level	300A to 850A at T _{case} = 125°	°C	-	0.86	V
	Threshold voltage – High level	850A to 4000A at T _{case} = 125	5°C	-	1.0	V
r _T	On-state slope resistance – Low level	300A to 850A at T _{case} = 125°C		-	0.611	mΩ
	On-state slope resistance – High level	850A to 4000A at T _{case} = 125°C		-	0.444	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3	μs
	,	$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, dl/dt	= 5A/µs,	-	800	μs
		dV _{DR} /dt = 20V/μs linear to 2000V				
Qs	Stored charge	$I_T = 1000A$, $tp = 1000us$, $T_i = 125$ °C,		2000	3500	μC
I _{RR}	Reverse recovery current	dI/dt =5A/μs,		81	121	Α
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	Α
lн	Holding current	$T_j = 25^{\circ}\text{C}, R_{G-K} = \infty, I_{TM} = 50$	0A, I _T = 5A	-	300	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25$ °C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25$ °C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

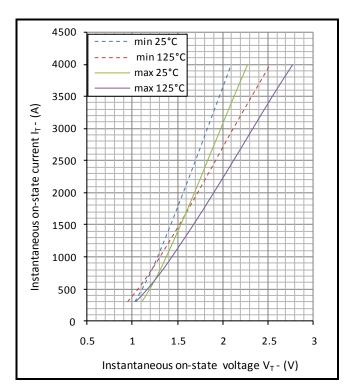


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

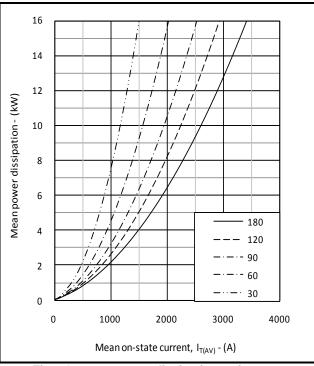
Where A = 0.259886

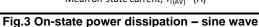
B = 0.122742

C = 0.000418

D = -0.002452

these values are valid for $T_j = 125^{\circ}C$ for $I_T 300A$ to 4000A





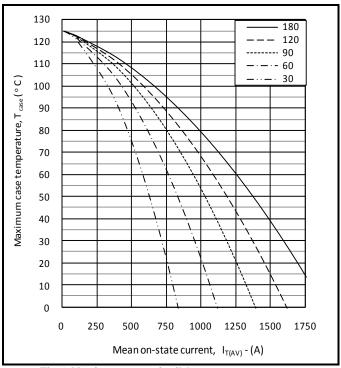


Fig.4 Maximum permissible case temperature, double side cooled - sine wave

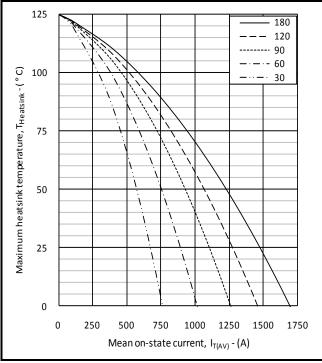


Fig.5 Maximum permissible heatsink temperature, double side cooled - sine wave

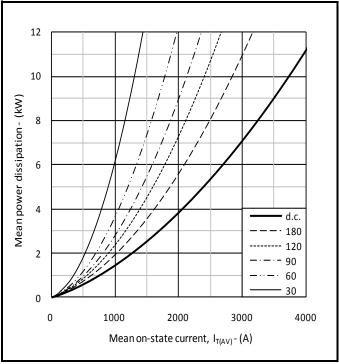


Fig.6 On-state power dissipation - rectangular wave

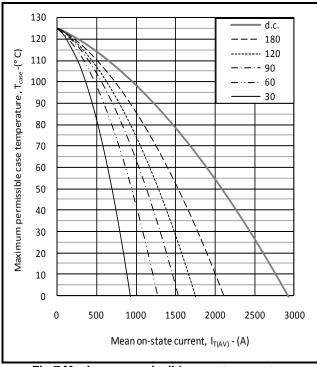


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

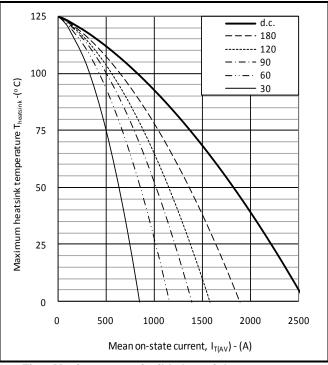
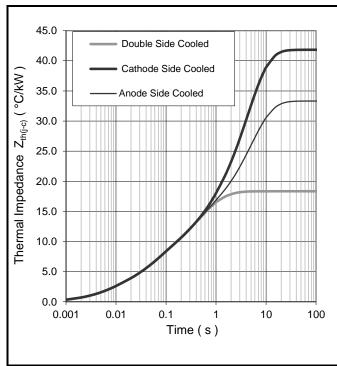


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	7.5608	4.0772	3.8420	2.8671
	T _i (s)	0.6877	0.2537	0.0614	0.0101
Anode side cooled	R _i (°C/kW)	6.7211	4.6219	15.5387	14.8631
	T _i (s)	0.1910	0.0158	5.0011	3.3169
Cathode side cooled	R _i (°C/kW)	11.5564	8.5810	4.7942	8.3643
	T: (s)	4 2216	6.0269	0.0166	0.2255

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(T/T_i))]$$

$\Delta R_{th(j-c)}$ Conduction

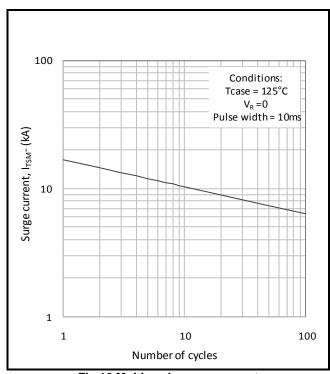
Tables show the increments of thermal resistance $R_{\text{th}(j\text{-}c)}$ when the device operates at conduction angles other than d.c.

	Double side co	oling		
	ΔZ_{th} ((z)		
θ°	sine.	rect.	ĺ	θ°
180	3.19	2.14	ĺ	180
120	3.72	3.10	Ī	120
90	4.29	3.64		90
60	4.81	4.23	Ī	60
30	5.22	4.88		30
15	5.40	5 22	ĺ	15

	Tilloac Olac	triode olde cooling			
	ΔZ_{th} (z)				
θ°	sine. rect.				
180	2.97	2.03			
120	3.43	2.89			
90	3.92	3.36			
60	4.36	3.87			
30	4.69	4.41			
15	4.84	4.70			

Ca	tribue Sided Cooling			
	ΔZ_{th} (z)			
θ°	sine.	rect.		
180	2.95	2.02		
120	3.40	2.87		
90	3.88	3.34		
60	4.31	3.84		
30	4.64	4.37		
15	4.79	4.65		

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)





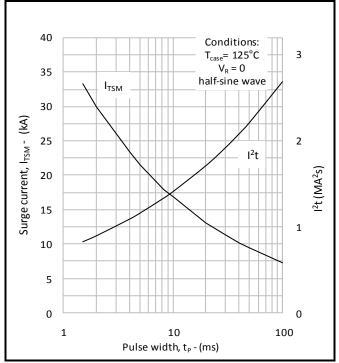


Fig.11 Single-cycle surge current

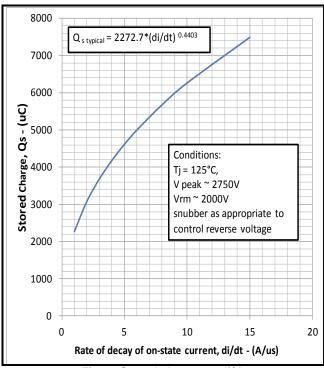


Fig.12 Stored charge vs di/dt

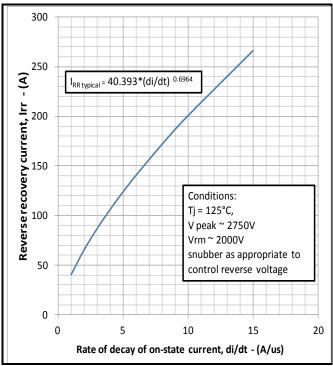


Fig.13 Reverse recovery current vs di/dt

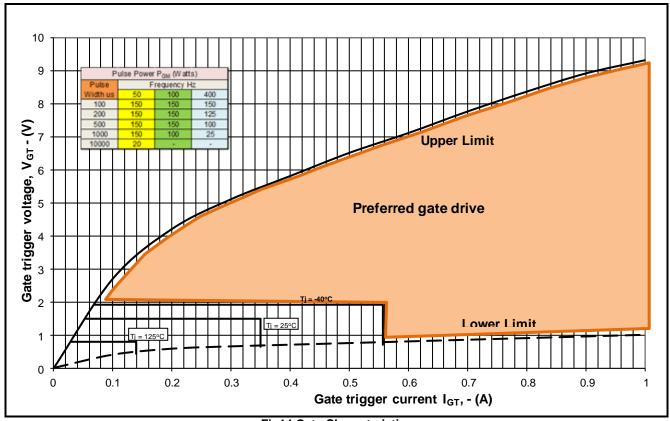


Fig14 Gate Characteristics

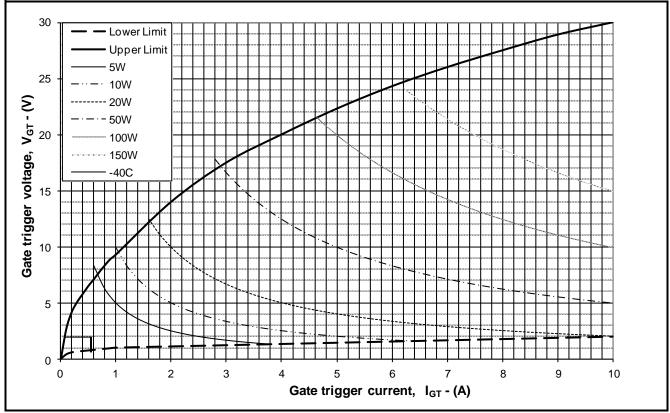


Fig. 15 Gate characteristics



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

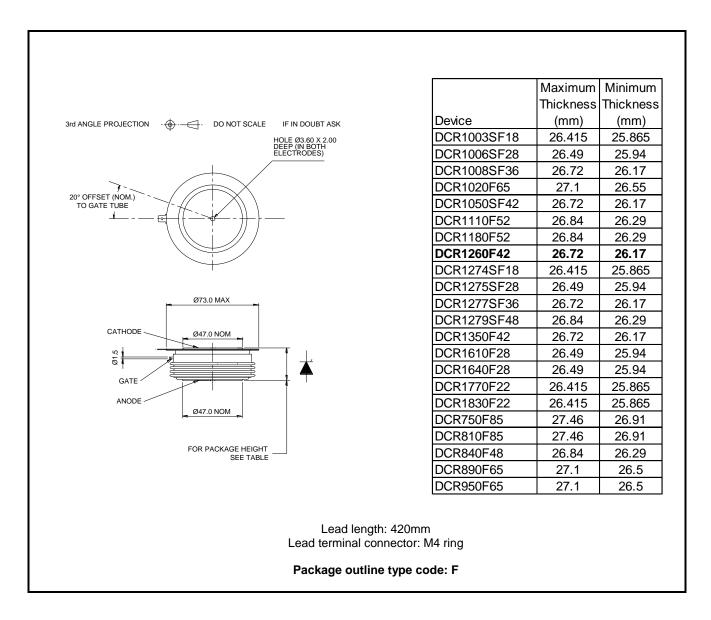


Fig.16 Package outline





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